

Title (en)

PROCESS FOR TUNGSTEN DEPOSITION BY PULSED GAS FLOW CVD

Title (de)

VERFAHREN ZUM ABSCHIEDEN VON WOLFRAM DURCH CVD MIT GEPULSTER GAS-EINSPEISUNG

Title (fr)

PROCEDE DE DEPOT DE TUNGSTENE PAR DEPOT CHIMIQUE EN PHASE VAPEUR A GAZ PULSE

Publication

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Application

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Abstract (en)

[origin: WO03064724A1] Embodiments of the present invention relate to a process of forming a nucleation layer on a substrate disposed in a processing chamber. One embodiment includes introducing one or more pulses of process gases, e.g., each pulse includes a hydrogen-containing gas and a tungsten-containing gas. The hydrogen-containing gas and the tungsten-containing gas can be removed from the processing chamber between the pulses by flowing a purge gas therebetween and/or pumping the chamber.

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